

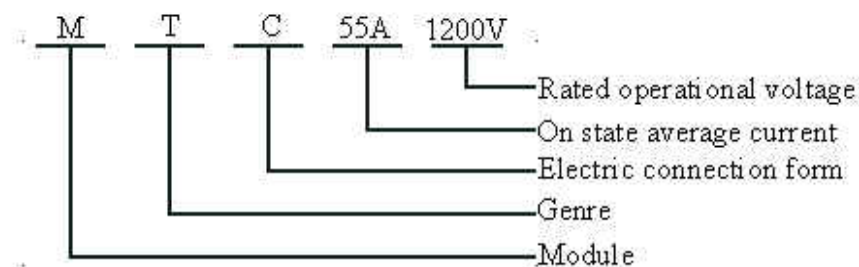
TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{RSM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C.})$			
V_{RRM}	25A	55A	90A	110A
800V	M25A800V	M55A800V	M90A800V	M110A800V
1200V	M25A1200V	M55A1200V	M90A 1200V	M110A1200V
1400V	M25A1400V	M55A1400V	M90A1400V	M110A1400V
1600V	M25A1600V	M55A1600V	M90A1600V	M110A1600V
1800V	M25A1800V	M55A1800V	M90A1800V	M110A1800V

ORDERING KEY



ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits				Units	Conditions
I_{TAV}	Average on-state current	25	55	90	110	A	$T_{VJ} = T_{VJM}$ 180°, sin.
I_{FAV}	Average forward current	25	55	90	110	A	
i^2t		800	9100	11860	20000	A ² s	$t=10\text{ mS } t=8.3\text{ mS}$ $T_J=45^{\circ}\text{C } 100\% V_{RRM}$
		730	8830	11300	19100	A ² s	
I_{ORMS}	Maximum RMS current	55	120	200	245	A	
I_{TSM} I_{FSM}	Surge current	400	1150	1700	2000	A	$t=10\text{ mS } t=8.3\text{ mS}$ $T_J=45^{\circ}\text{C } 100\% V_{RRM}$
		420	1200	1800	2150	A	

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I_{RRM}	Maximum repetitive peak reverse Leakage current	10	10	10	10	mA	$T_J=125^{\circ}\text{C}$,
I_{DRM}	Maximum repetitive peak off-state Leakage current						
V_{RRM}	Maximum repetitive peak reverse voltage	800-1800				V	$125^{\circ}\text{C } I_{RRM}, I_{DRM} \leq 10\text{Ma}$
V_{DRM}	Maximum repetitive peak off-state voltage						
V_{TM}	Peak value on-state voltage	1.6	1.57	1.6	1.6	V	$I_{TM}=\pi I_{TAV}; I_{FM}=\pi I_{FAV}$ $T_J=25^{\circ}\text{C}$
V_{FM}	Peak value forward voltage	1.6	1.57	1.6	1.6		
di/dt	Critical rate of rise of on-state current	150				A/ μS	$T_J=25^{\circ}\text{C}, 0.67 V_{DRM} I_g=500\text{mA}$ $t_r < 0.5\mu\text{S}, t_p > 6\mu\text{S}$
dv/dt	Critical rate of rise of on-state voltage	500				V/ μS	$T_J=125^{\circ}\text{C}, 0.67 V_{DRM}$
I_H	Holding voltage	200				mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_L	Latching current	400				mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
P_{GM}	Peak gate power dissipation	10				W	
I_{GM}	Peak gate power current	2.5				A	
V_{GT}	Gate trigger voltage	≤ 1.5				V	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_{GT}	Gate trigger current	≤ 100				mA	
V_{ISO}	Insulation test voltage	2500				V	50Hz, t=1min
T_J	Junction temperature	- 40to125				$^{\circ}\text{C}$	
T_{stg}	Storage temperature						
R_{thJC}	Thermal resistance junction to case	0.44	0.25	0.15	0.13	$^{\circ}\text{C}/\text{W}$	Per module, DC
R_{thCS}	Thermal resistance case to heat-sink	0.1				$^{\circ}\text{C}/\text{W}$	Per module, DC
Wt	Weight	150				g	
	Size	94×25×38				mm	
	Colour	Black					

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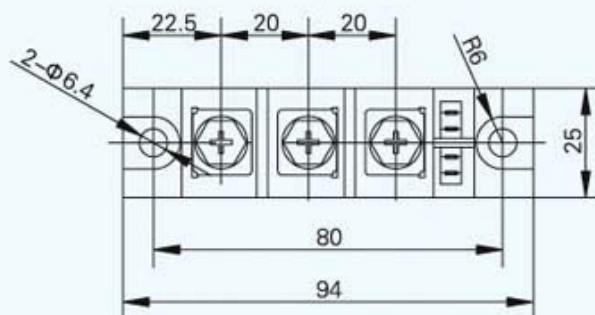
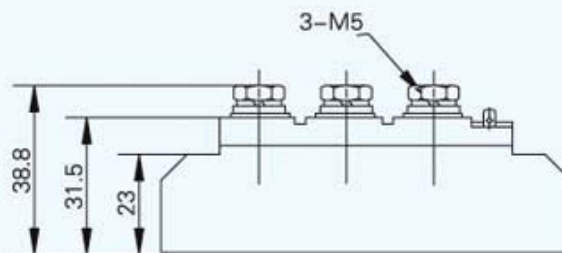
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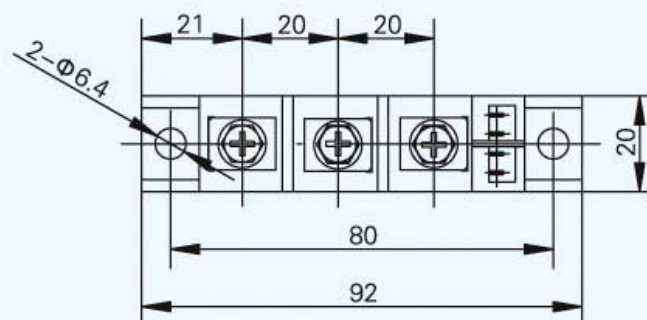
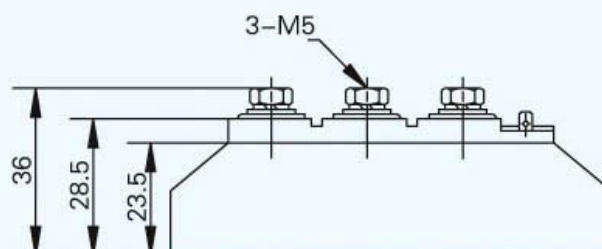
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TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{DRM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C},)$		
V_{RRM}	25A	55A	90A
800V	M25A800V	M55A800V	M90A800V
1200V	M25A1200V	M55A1200V	M90A 1200V
1400V	M25A1400V	M55A1400V	M90A1400V
1600V	M25A1600V	M55A1600V	M90A1600V
1800V	M25A1800V	M55A1800V	M90A1800V



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ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits			Units	Conditions
I_{TAV}	Average on-state current	25	55	90	A	$T_{VJ} = T_{VJM}$
I_{FAV}	Average forward current	25	55	90	A	180°, sin.
I^2t		800 730	9100 8830	11850 11300	A^2s A^2s	$t=10\text{ mS } T_J=45^\circ C$ $t=8.3\text{ mS } T_J=45^\circ C 100\% V_{RRM}$
I_{ORMS}	Maximum RMS current	55	120	200	A	AC switch
I_{TSM} I_{FSM}	Surge current	400 420	1150 1200	1700 1800	A A	$t=10\text{ mS } T_J=45^\circ C$ $t=8.3\text{ mS } T_J=45^\circ C 100\% V_{RRM}$
I_{RRM} I_{DRM}	Maximum repetitive peak reverse Leakage current Maximum repetitive peak off-state Leakage current	10	10	10	mA	$T_J=125^\circ C$,
V_{RRM} V_{DRM}	Maximum repetitive peak reverse voltage Maximum repetitive peak off-state voltage	800-1800			V	$125^\circ C, I_{RRM}, I_{DRM} \leq 10\text{mA}$
V_{TM} V_{FM}	Peak value on-state voltage Peak value forward voltage	1.6 1.6	1.57 1.57	1.6 1.6	V	$I_{TM} = \pi I_{TAV}; I_{FM} = \pi I_{FAV}$ $T_J=25^\circ C$
di/dt	Critical rate of rise of on-state current	150			A/ μS	$T_J=125^\circ C, 0.67 V_{DRM} I_g=500\text{mA}$
dv/dt	Critical rate of rise of on-state voltage	500			V/ μS	$T_J=125^\circ C, 0.67 V_{DRM}$
I_H	Holding current	200			mA	$T_J=25^\circ C$ Anode voltage=6V
I_L	Latching current	400			mA	$T_J=25^\circ C$ Anode voltage=6V
P_{GM}	Peak gate power dissipation	10			W	
I_{GM}	Peak gate power current	2.5			A	
V_{GT}	Gate trigger voltage	≤ 1.5			V	$T_J=25^\circ C$ Anode voltage=6v
I_{GT}	Gate trigger current	≤ 100			mA	$T_J=25^\circ C$ Anode voltage=6v
V_{ISO}	Insulation test voltage	2500			Vrms	50Hz, $t=1\text{min}$,
T_J T_{stg}	Junction temperature Storage temperature	- 40to125			$^\circ C$	
R_{thJC}	Thermal resistance junction to case	0.44	0.25	0.15	$^\circ C/W$	Per module, DC
R_{thCS}	Thermal resistance case to heat-sink	0.1			$^\circ C/W$	Per module, DC

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Series M

25 to 90 Amps Module

Wt	Weight(typical)	120	g	
	Size	92×20×36	mm	
	Colour	Black		

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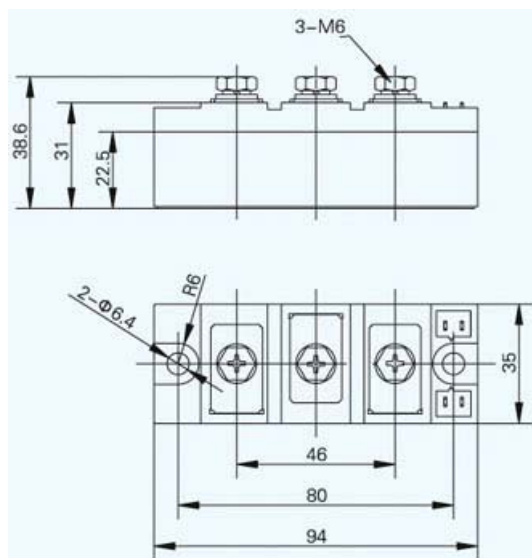
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TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{RSM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C.})$		
V_{RRM}	130A	160A	180A
800V	M130A800V	M160A800V	M180A800V
1200V	M130A1200V	M160A1200V	M180A 1200V
1400V	M130A1400V	M160A1400V	M180A1400V
1600V	M130A1600V	M160A1600V	M180A1600V
1800V	M130A1800V	M160A1800V	M180A1800V



ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits			Units	Conditions
I_{TAV}	Average on-state current	130	160	180	A	$T_{VJ} = T_{VJM}$ 180° , sin.
I_{FAV}	Average forward current		160	180	A	
i^2t		51	113	130	KA^2s	$t=10\text{ mS } t=8.3\text{ mS}$
		47	103	120	KA^2s	$T_J=45^{\circ}\text{C } 100\% V_{RRM}$
I_{ORMS}	Maximum RMS current	290	355	400	A	

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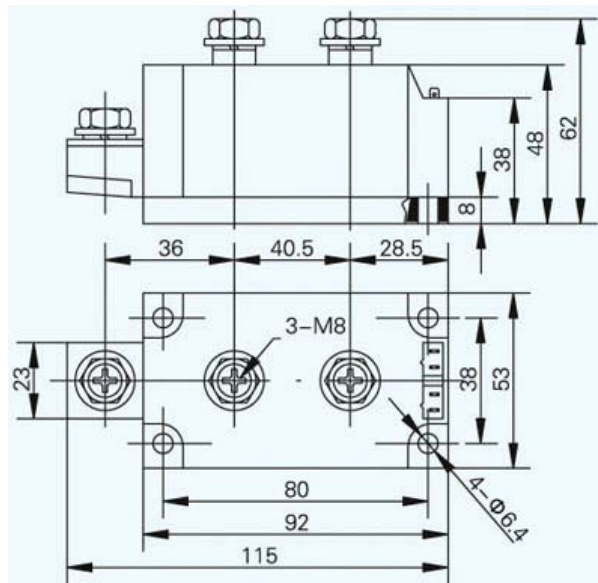
I _{TSM} I _{FSM}	Surge current	3200 3650	4750 5000	5100 5400	A A	t=10 mS t=8.3 mS T _J =45℃ 100% V _{RRM}
I _{RRM} I _{DRM}	Maximum repetitive peak reverse Leakage current Maximum repetitive peak off-state Leakage current	10	10	10	mA	T _J =125℃,
V _{RRM}	Maximum repetitive peak reverse voltage	800-1800			V	125℃ I _{RRM} , I _{DRM} =10mA
V _{DRM}	Maximum repetitive peak off-state voltage					
V _{TM} V _{FM}	Peak value on-state voltage Peak value forward voltage	1.6 1.6	1.6 1.6	1.9	V	I _{TM} =πI _{TAV} ; I _{FM} =πI _{FAV} T _J =25℃
di/dt	Critical rate of rise of on-state current	150			A/μs	T _J =25℃,0.67V _{DRM} .,I _{TM} =I _{TAV} , I _g =500mA tr<0.5μs, t _p >6μs
dv/dt	Critical rate of rise of on-state voltage	500			V/μs	T _J =125℃, 0.67 V _{DRM}
I _H	Holding current	200			mA	T _J =25℃ Anode voltage=6v
I _L	Latching current	400			mA	T _J =25℃ Anode voltage=6v
P _{GM}	Peak gate power dissipation	120			W	T _J =T _{JM} ;I _T =I _{TAV} ;T _P =30μs
V _{GT}	Peak gate power current	≤2			V	T _J =25℃ Anode voltage=6v
I _{GT}	Gate trigger voltage	≤100			mA	
V _{ISO}	Gate trigger current	2500			V	50Hz,t=1min
T _J	Insulation test voltage	- 40to125			℃	
T _{stg}	Junction temperature				℃	
R _{thJC}	Storage temperature	0.12	0.11	0.11	K/W	Per module, DC
R _{thCS}	Thermal resistance junction to case	0.07			K/W	Per module, DC
Wt	Thermal resistance case to heat-sink	362			g	
	Size	94×35×38			mm	
	Colour	Black				

TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{RSM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C}.)$		
V_{RRM}	200A	250A	300A
800V	M200A800V	M250A800V	M300A800V
1200V	M200A1200V	M250A1200V	M300A 1200V
1400V	M200A1400V	M250A1400V	M300A1400V
1600V	M200A1600V	M250A1600V	M300A1600V
1800V	M200A1800V	M250A1800V	M300A1800V



ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits			Units	Conditions
I_{TAV}	Average on-state current	200	250	300	A	$T_{VJ} = T_{VJM}$ 180°, sin.
I_{FAV}	Average forward current	200	250	300	A	
I^2t		180	245	304	KA ² s	t=10 mS $T_J=45^{\circ}\text{C}$
		180	245	300	KA ² s	t=8.3 mS $T_J=45^{\circ}\text{C}$ 100% V_{RRM}

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I_{TSM} I_{FSM}	Surge current I	6000 6000	7000 7600	7800 8500	A A	t=10 mS t=8.3 Ms
I_{RRM} I_{DRM}	Maximum repetitive peak reverse Leakage current Maximum repetitive peak off-state Leakage current	≤ 15			mA	$T_J=125^{\circ}\text{C}$,
V_{RRM} V_{DRM}	Maximum repetitive peak reverse voltage Maximum repetitive peak off-state voltage	800-1800			V	$125^{\circ}\text{C } I_{RRM}, I_{DRM}=10\text{mA}$
V_{TM} V_{FM}	Peak value on-state voltage Peak value forward voltage	≤ 1.9	≤ 1.9	≤ 1.9	V	$I_{TM}=\pi I_{TAV}; I_{FM}=\pi I_{FAV}$ $T_J=25^{\circ}\text{C}$
di/dt	Critical rate of rise of on-state current	150			A/ μs	$T_J=25^{\circ}\text{C}, 0.67V_{DRM}, I_g=500\text{mA}$ $tr<0.5\mu\text{s}, t_p>6\mu\text{s}$
dv/dt	Critical rate of rise of on-state voltage	500			V/ μs	$T_J=125^{\circ}\text{C}, 0.67 V_{DRM}$
I_H	Holding current	200			mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_L	Latching current	400			mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
P_{GM}	Peak gate power dissipation	10	10	12	W	
I_{GM}	Peak gate power current	2.5	2.5	3	A	
V_{GT}	Gate trigger voltage	≤ 2			V	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_{GT}	Gate trigger current	≤ 100			mA	
V_{ISO}	Insulation test voltage	2500			V	50Hz, t=1min
T_J T_{stg}	Junction temperature Storage temperature	- 40to125			$^{\circ}\text{C}$ $^{\circ}\text{C}$	
R_{thJC}	Thermal resistance junction to case	0.10	0.09	0.08	K/W	Per module, DC
R_{thCS}	Thermal resistance case to heat-sink	0.05			K/W	Per module, DC
Wt	Weight(typical)	865			G	
	Size	115×53×62			Mm	
	Colour	Black				

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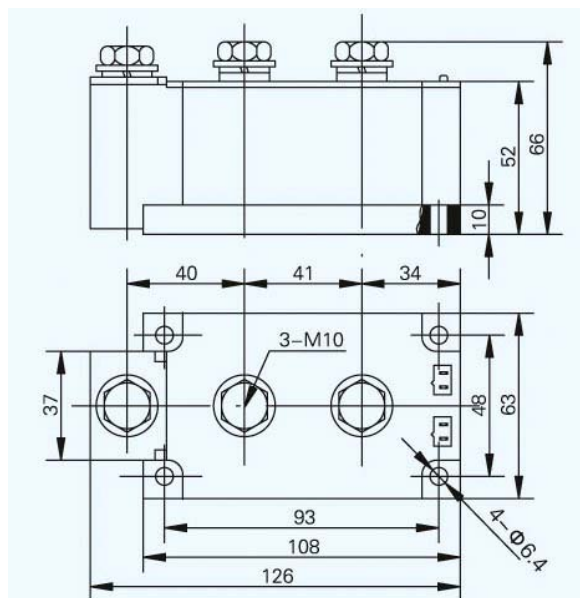
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TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{RSM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C.})$		
V_{RRM}	350A	400A	500A
800V	M350A800V	M400A800V	M500A800V
1200V	M350A1200V	M400A1200V	M500A 1200V
1400V	M350A1400V	M400A1400V	M500A1400V
1600V	M350A1600V	M400A1600V	M500A1600V
1800V	M350A1800V	M400A1800V	M500A1800V



ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits			Units	Conditions
I_{TAV}	Average on-state current	350	400	500	A	$T_{VJ} = T_{VJM}$
I_{FAV}	Average forward current	350	400	500	A	180°, sin.
i^2t		330	400	450	KA ² s	t=10 mS
		330	400	450	KA ² s	t=8.3 mS
I_{TSM}	Surge current	8400	9100	9500	A	t=10 mS
I_{FSM}		9000	9800	11000	A	t=8.3 mS

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I_{RRM}	Maximum repetitive peak reverse Leakage current	15	20		mA	$T_J=125^{\circ}\text{C}$,
I_{DRM}	Maximum repetitive peak off-state Leakage current					
V_{RRM}	Maximum repetitive peak reverse voltage	800-1800			V	$125^{\circ}\text{C } I_{RRM}$, $I_{DRM}=10\text{mA}$
V_{DRM}	Maximum repetitive peak off-state voltage	800-1800				
V_{TM}	Peak value on-state voltage	1.9	1.90	1.90	V	$I_{TM}=\pi I_{TAV}$; $I_{FM}=\pi I_{FAV}$ $T_J=25^{\circ}\text{C}$
V_{FM}	Peak value forward voltage		1.50	1.50		
di/dt	Critical rate of rise of on-state current	150			A/ μs	$T_J=25^{\circ}\text{C}$, $0.67V_{DRM,,}$ $I_g=500\text{mA}$ $t_r<0.5\mu\text{s}$, $t_p>6\mu\text{s}$
dv/dt	Critical rate of rise of on-state voltage	500			V/ μs	$T_J=125^{\circ}\text{C}$, $0.67 V_{DRM}$
I_H	Holding current	200			mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_L	Latching current	400			mA	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
P_{GM}	Peak gate power dissipation	10	12	12	W	
I_{GM}	Peak gate power current	2.5	3	3	A	
V_{GT}	Gate trigger voltage	≤ 2			V	$T_J=25^{\circ}\text{C}$ Anode voltage=6v
I_{GT}	Gate trigger current	≤ 100			mA	
V_{ISO}	Insulation test voltage	2500			V	50Hz t=1s
T_J	Junction temperature	- 40to125			$^{\circ}\text{C}$	
T_{stg}	Storage temperature				$^{\circ}\text{C}$	
R_{thJC}	Thermal resistance junction to case	0.07	0.065	0.06	K/W	Per module, DC
R_{thCS}	Thermal resistance case to heat-sink	0.02			K/W	Per module, DC
Wt	Weight(typical)	1509	1509	1509	G	
	Size	126×63×66			mm	
	Colour	Black				

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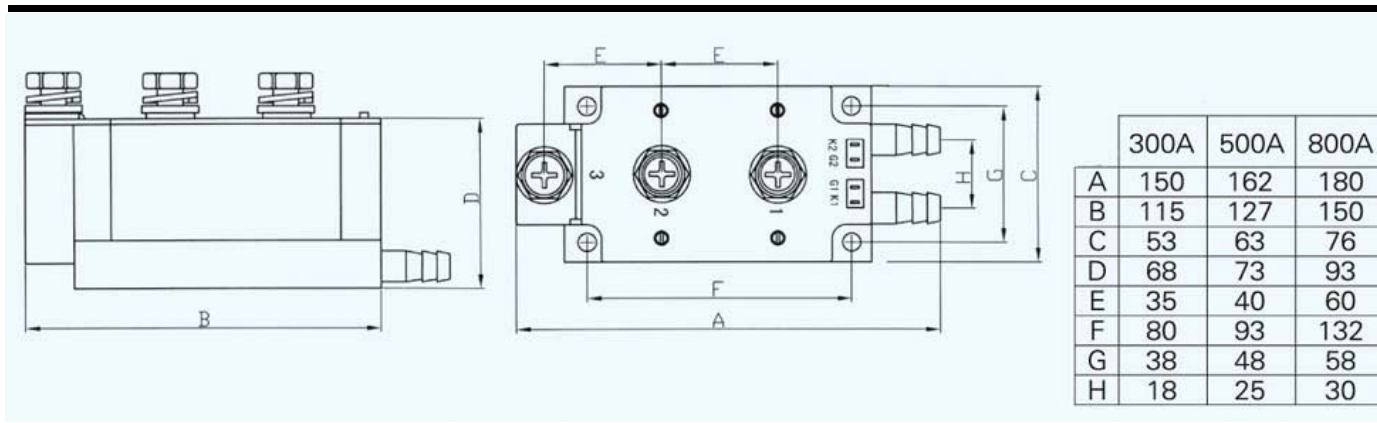
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TYPICAL APPLICATIONS

- Commute power supply
- Switch with no contact
- Battery charge or discharge
- Temperature control for industrial calefaction
- Electric welding, Transducer

PRELIMINARY DATA SHEET

V_{RSM}	$I_{DAV}(T_{case}= 100\text{ }^{\circ}\text{C},)$		
V_{RRM}	500A	600A	800A
800V	M500A800V	M600A800V	M800A800V
1200V	M500A1200V	M600A1200V	M800A 1200V
1400V	M500A1400V	M600A1400V	M800A1400V
1600V	M500A1600V	M600A1600V	M800A1600V
1800V	M500A1800V	M600A1800V	M800A1800V



ELECTRICAL SPECIFICATIONS

Symbol	Specifications Names	Specifications Limits			Units	Conditions
I_{TAV}	Average on-state current	500	600	800	A	$T_{VJ} = T_{VJM}$
I_{FAV}	Average forward current	500	600	800	A	$180^{\circ}, \sin.$
I^2t		455	583	1037	KA^2s	$t=10\text{ mS } T_J=45^{\circ}\text{C}$
		456	583	1037	KA^2s	$t=8.3\text{ mS } T_J=45^{\circ}\text{C } 100\% V_{RRM}$
I_{TSM}	Surge current	8400	9100	9500	A	$t=10\text{ mS } T_J=45^{\circ}\text{C}$
I_{FSM}		9000	9800	11000	A	$t=8.3\text{ mS } T_J=45^{\circ}\text{C } 100\% V_{RRM}$
I_{RRM}	Maximum repetitive peak reverse Leakage current	20	35		mA	$T_J=125^{\circ}\text{C},$
I_{DRM}	Maximum repetitive peak off-state Leakage current					

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V _{RRM}	Maximum repetitive peak reverse voltage	800-1800			V	125℃I _{RRM} , I _{DRM} =20-35mA
V _{DRM}	Maximum repetitive peak off-state voltage	800-1800				
V _{TM} V _{FM}	Peak value on-state voltage Peak value forward voltage	1.9 1.9	1.9 1.9	1.9 1.9	V	I _{TM} =πI _{TAV} ; I _{FM} =πI _{FAV} T _J =25℃
di/dt	Critical rate of rise of on-state current	150			A/μs	T _J =25℃,0.67V _{DRM} ,I _g =500mA
dv/dt	Critical rate of rise of on-state voltage	500			V/μs	T _J =125℃, 0.67 V _{DRM}
I _H	Holding current	200			mA	T _J =25℃Anode voltage=6v
I _L	Latching current	400			mA	T _J =25℃Anode voltage=6v
P _{GM}	Peak gate power dissipation	12	12	14	W	
I _{GM}	Peak gate power current	3	3	4	A	
V _{GT}	Gate trigger voltage	3			V	T _J =25℃ Anode voltage=6v
I _{GT}	Gate trigger current	150			mA	
V _{ISO}	Insulation test voltage	2500			Vrms	50Hz , t=1min
T _J	Junction temperature	- 40to125			℃	
T _{stg}	Storage temperature					
R _{thJC}	Thermal resistance junction to case	0.06	0.06	0.04	K/W	Per module, DC
R _{thCS}	Thermal resistance case to heat-sink	0.015			K/W	Per module, DC
Wt	Weight(typical)	1061	1650	3108	g	
	Size				mm	
	Colour	Black				
		Water-cooling				



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